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NPN-Silizium-Fototransistor Silicon NPN Phototransistor

SFH 309 P
SFH 309 PFA



SFH 309 P



SFH 309 PFA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 380 nm bis 1180 nm (SFH 309 P) und bei 880 nm (SFH 309 PFA)
- Hohe Linearität
- 3 mm plane Plastikbauform im LED-Gehäuse
- Gruppiert lieferbar

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 380 nm to 1180 nm (SFH 309 P) and of 880 nm (SFH 309 PFA)
- High linearity
- 3 mm LED plastic package
- Available in groups

Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 309 P	Q62702-P245
SFH 309 PFA	Q62702-P246

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	– 40 ... + 100	°C
Löttemperatur bei Tauchlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 5$ s Dip soldering temperature ≥ 2 mm distance from case bottom, soldering time $t \leq 5$ s	T_S	260	°C
Löttemperatur bei Kolbenlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 3$ s Iron soldering temperature ≥ 2 mm distance from case bottom, soldering time $t \leq 3$ s	T_S	300	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	35	V
Kollektorstrom Collector current	I_C	15	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	I_{CS}	75	mA
Verlustleistung, $T_A = 25 \text{ °C}$ Total power dissipation	P_{tot}	165	mW
Wärmewiderstand Thermal resistance	R_{thJA}	450	K/W

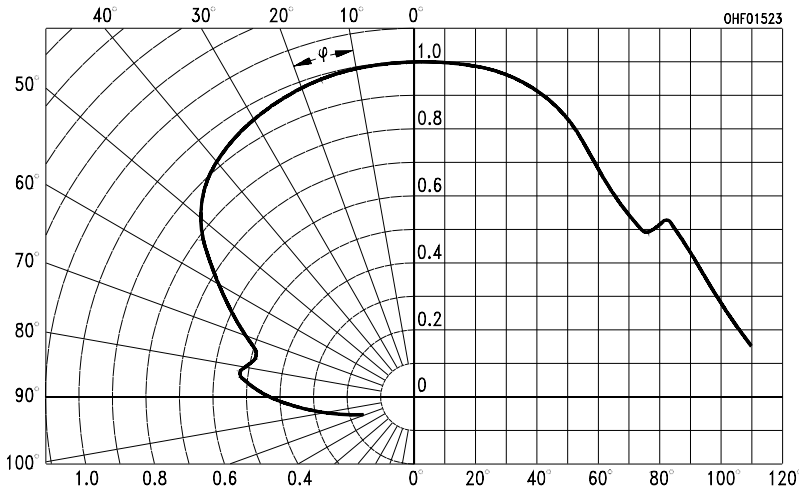
Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

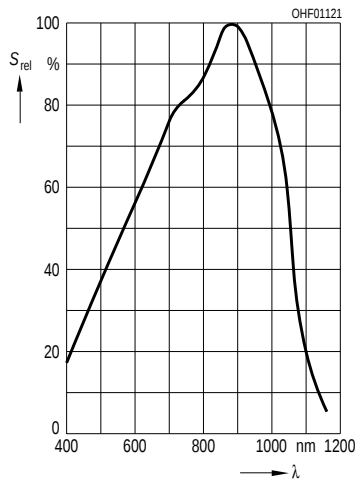
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 309 P	SFH 309 PFA	
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	860	900	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	380 ... 1180	730 ... 1120	nm
Bestrahlungsempfindliche Fläche ($\varnothing 220\text{ }\mu\text{m}$) Radiant sensitive area	A	0.038	0.038	mm^2
Abmessungen der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.45×0.45	0.45×0.45	$\text{mm} \times \text{mm}$
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	0.4 ... 0.8	0.4 ... 0.8	mm
Halbwinkel Half angle	φ	± 75	± 75	Grad deg.
Kapazität, $V_{\text{CE}} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_{CE}	5.0	5.0	pF
Dunkelstrom Dark current $V_{\text{CE}} = 25\text{ V}$, $E = 0$	I_{CEO}	1 (≤ 200)	1 (≤ 200)	nA

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotostrom, $\lambda = 950\text{ nm}$ Photocurrent $E_e = 0.5\text{ mW/cm}^2$, $V_{CE} = 5\text{ V}$ SFH 309 P: $E_v = 1000\text{ lx}$, Normlicht/standard light A, $V_{CE} = 5\text{ V}$	I_{PCE} I_{PCE}	≥ 63 420	μA μA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 1\text{ k}\Omega$	t_r , t_f	6	μs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = 20\text{ }\mu\text{A}$, $E_e = 0.5\text{ mW/cm}^2$	V_{CEsat}	150	mV

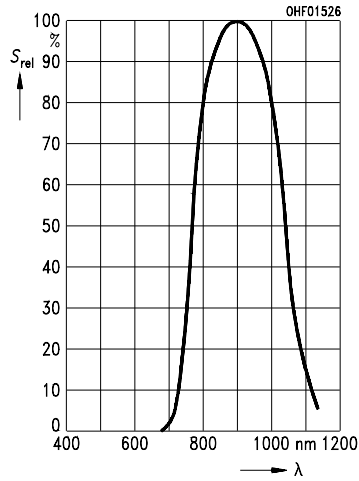
Directional Characteristics $S_{rel} = f(\varphi)$



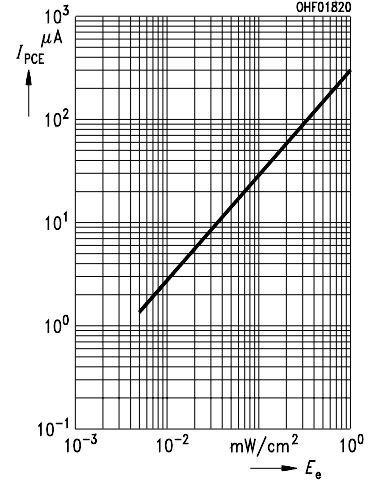
Relative Spectral Sensitivity,
SFH 309 P $S_{rel} = f(\lambda)$



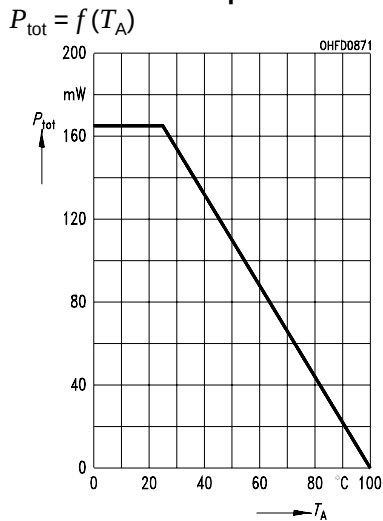
Relative Spectral Sensitivity,
SFH 309 PFA $S_{rel} = f(\lambda)$



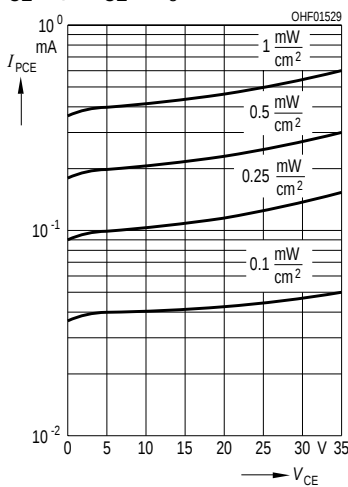
Photocurrent
 $I_{PCE} = f(E_e), V_{CE} = 5 \text{ V}$



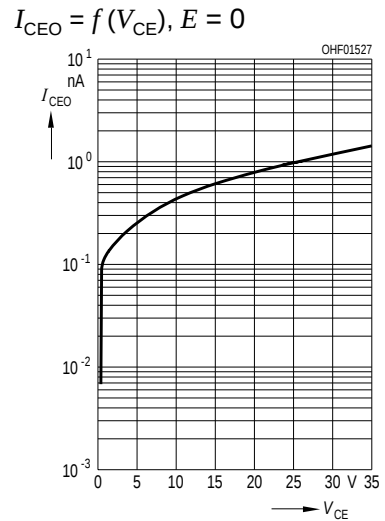
Total Power Dissipation



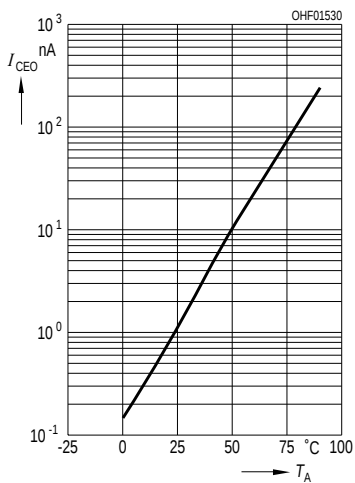
Photocurrent
 $I_{PCE} = f(V_{CE}), E_e = \text{Parameter}$



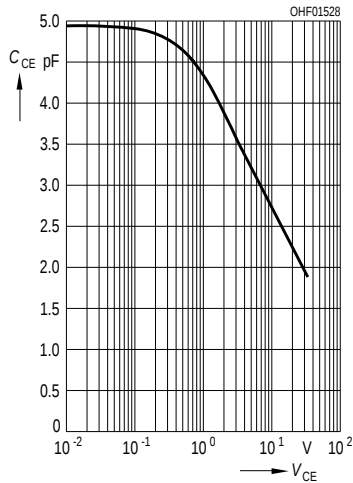
Dark Current



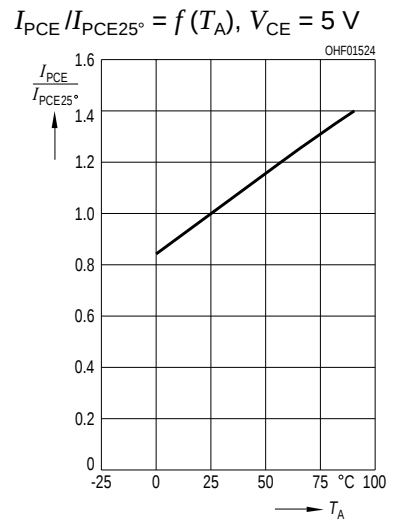
Dark Current
 $I_{CEO} = f(T_A), V_{CE} = 25 \text{ V}, E = 0$



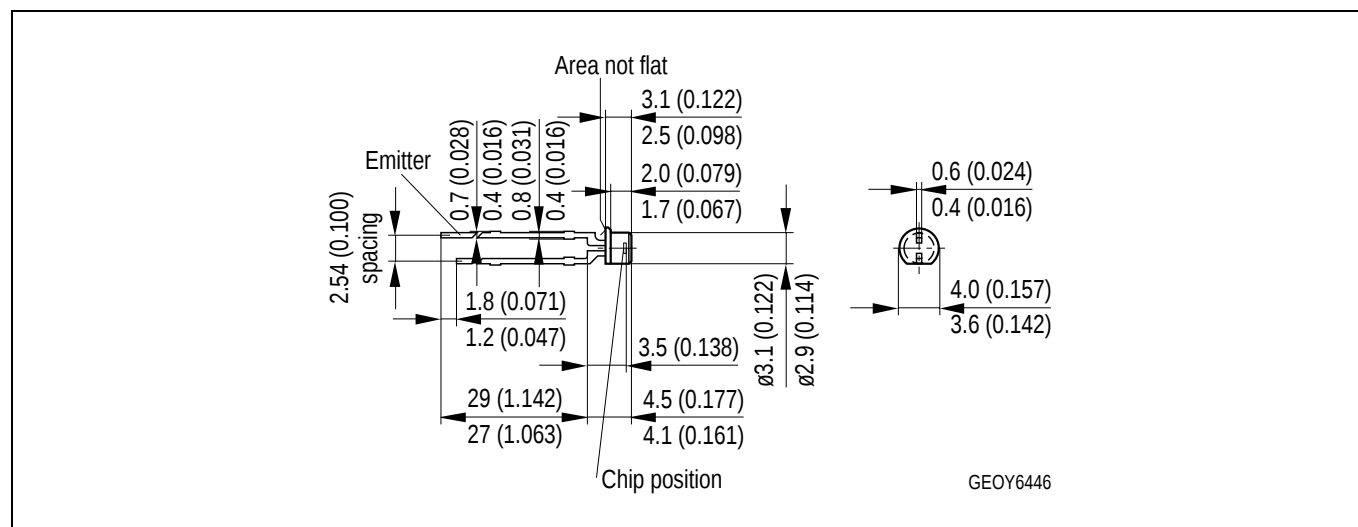
Capacitance
 $C_{CE} = f(V_{CE}), f = 1 \text{ MHz}, E = 0$



Photocurrent



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components¹, may only be used in life-support devices or systems² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.